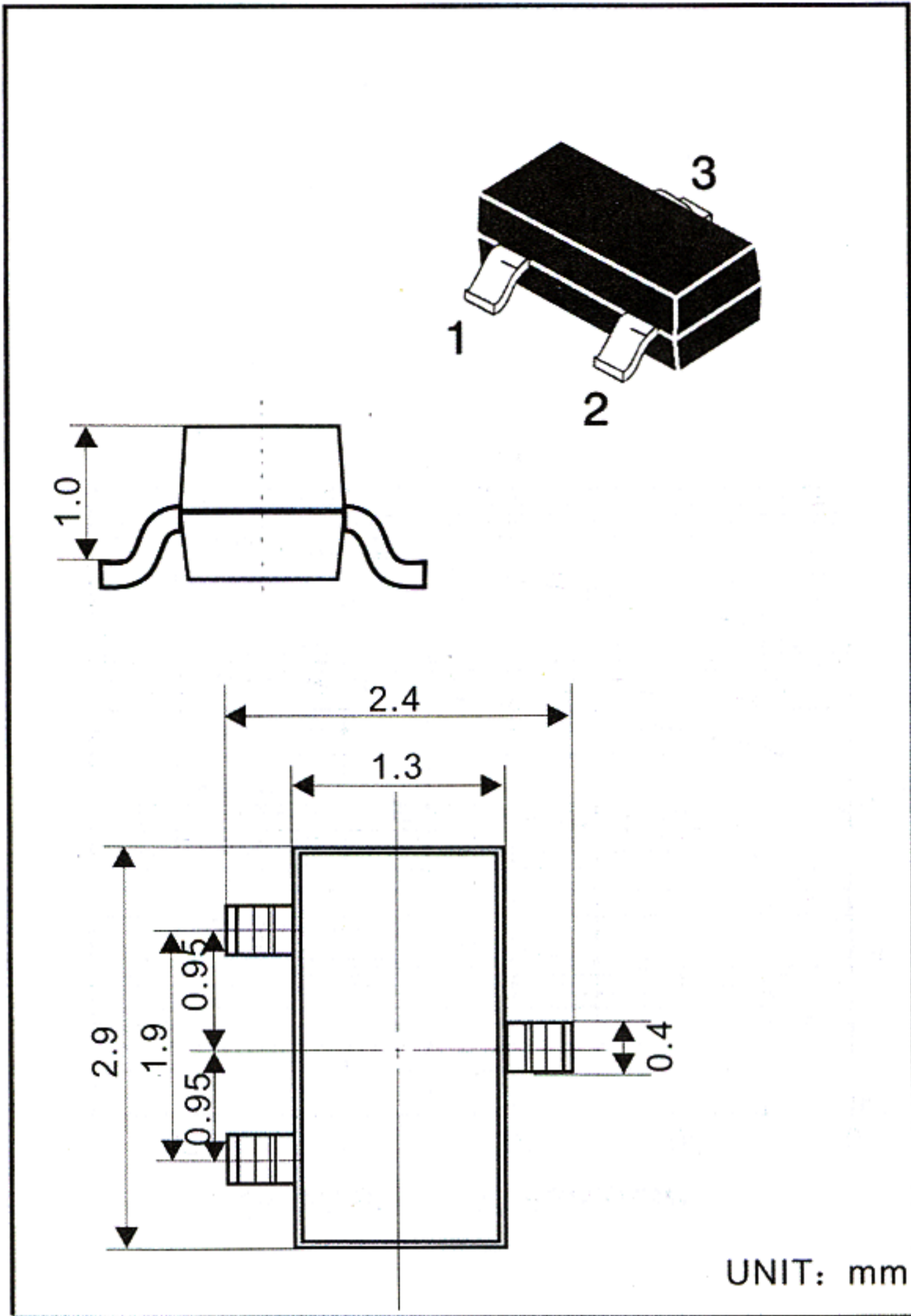


1SS181 SWITCHING DIODE



FEATURES

Power dissipation

P_D : 150mW ($T_{amb}=25^\circ C$)

Forward current

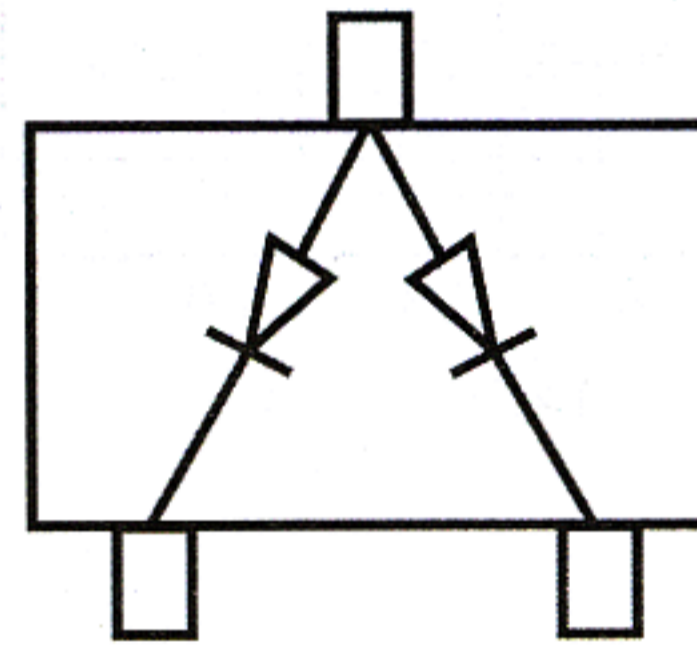
I_F : 100mA

Reverse voltage

V_R : 80V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^\circ C$ to $+150^\circ C$



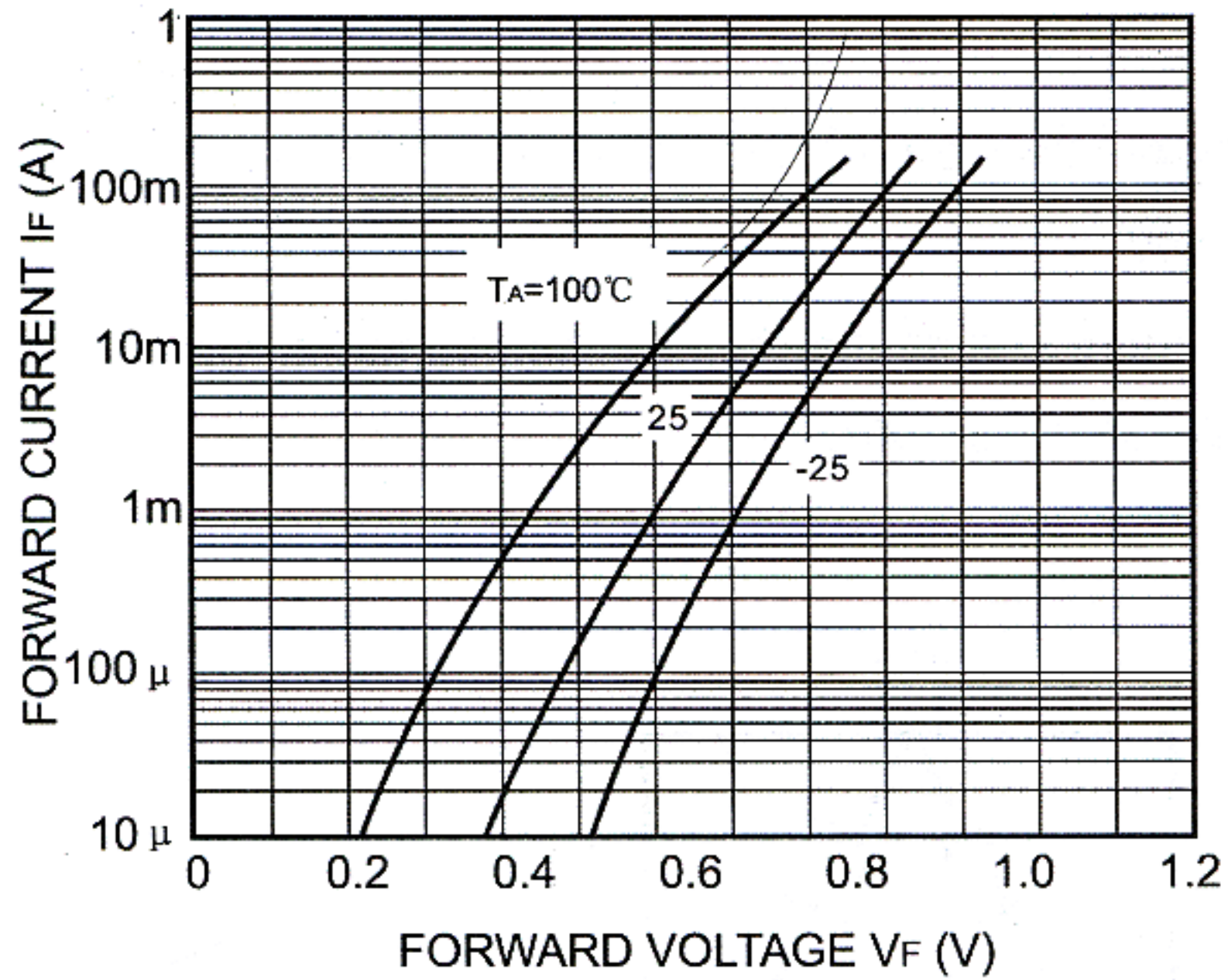
MARKING: A3

ELECTRICAL CHARACTERISTICS

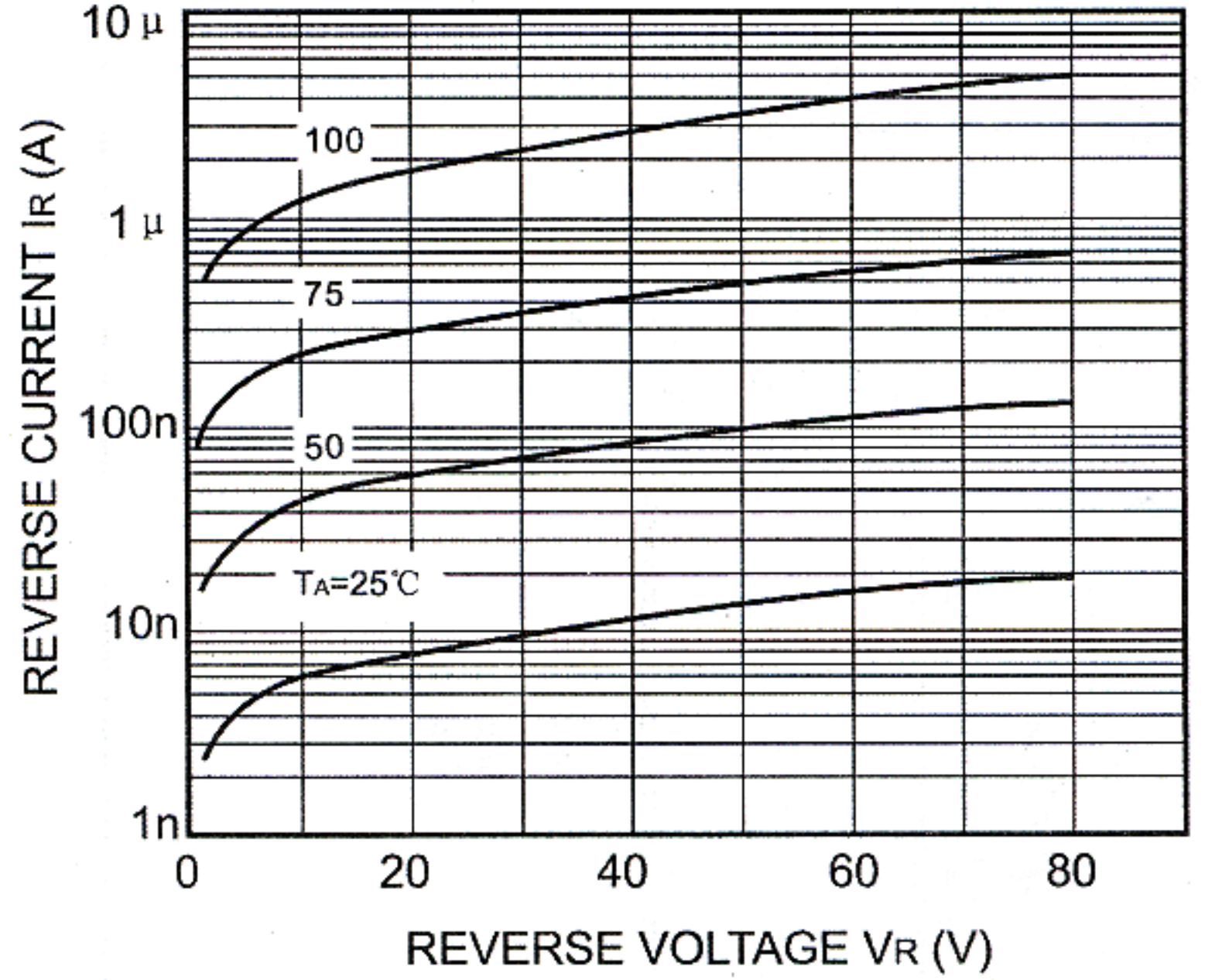
($T_{amp}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100 \mu A$	80		V
Reverse voltage leakage current	I_R	$V_R=80V$		0.5	μA
Forward voltage	V_F	$I_F=100mA$		1.2	V
Diode capacitance	C_{tot}	$V_R=0V, f=1MHz$		4	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1I_R$		4	ns

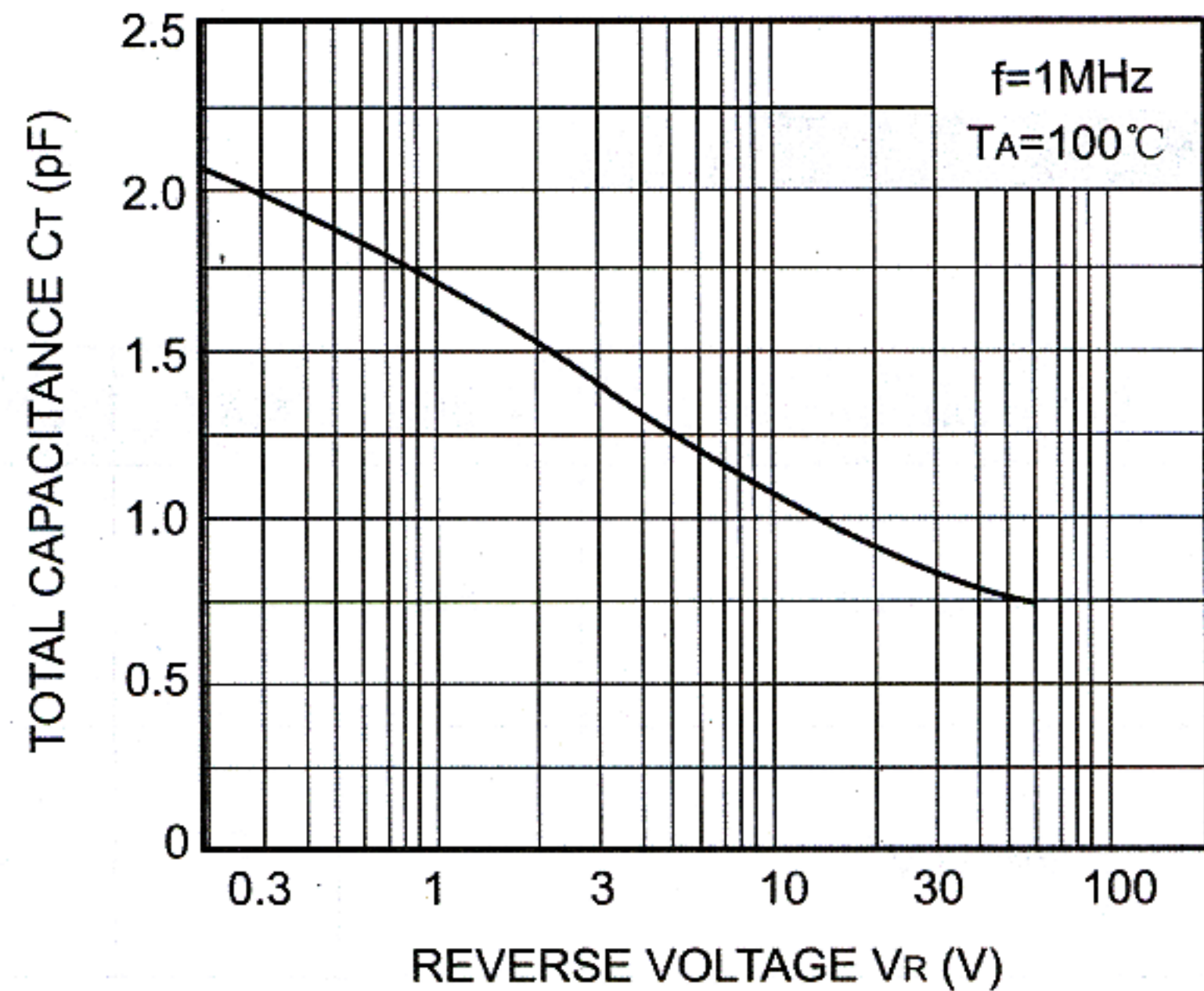
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



$t_{rr} - I_F$

